

International
IR Rectifier
RADIATION HARDENED
POWER MOSFET
THRU-HOLE (Low-Ohmic TO-254AA)

PD - 95840

IRHMS57163SE
JANSR2N7475T1
130V, N-CHANNEL
REF: MIL-PRF-19500/685

R5™ TECHNOLOGY

Product Summary

Part Number	Radiation Level	R _{DS(on)}	I _D	QPL Part Number
IRHMS57163SE	100K Rads (Si)	0.0145Ω	45A*	JANSR2N7475T1



International Rectifier's R5™ technology provides high performance power MOSFETs for space applications. These devices have been characterized for Single Event Effects (SEE) with useful performance up to an LET of 80 (MeV/(mg/cm²)). The combination of low R_{DS(on)} and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features:

- Low R_{DS(on)}
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Ceramic Eyelets
- Electrically Isolated
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I _D @ V _{GS} = 12V, T _C = 25°C	Continuous Drain Current	45*	A
I _D @ V _{GS} = 12V, T _C = 100°C	Continuous Drain Current	45*	
I _{DM}	Pulsed Drain Current ①	180	W
P _D @ T _C = 25°C	Max. Power Dissipation	208	
	Linear Derating Factor	1.67	W/C
V _{GS}	Gate-to-Source Voltage	±20	V
E _{AS}	Single Pulse Avalanche Energy ②	432	mJ
I _{AR}	Avalanche Current ①	45	A
E _{AR}	Repetitive Avalanche Energy ①	20.8	mJ
dV/dt	Peak Diode Recovery dV/dt ③	11.3	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in.(1.6 mm from case for 10s))	g
	Weight	9.3 (Typical)	

* Current is limited by package

For footnotes refer to the last page

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Pre-Irradiation
Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	130	—	—	V	$\text{V}_{\text{GS}} = 0\text{V}, \text{ID} = 1.0\text{mA}$
$\Delta \text{BV}_{\text{DSS}}/\Delta T_j$	Temperature Coefficient of Breakdown Voltage	—	0.16	—	$\text{V}/^\circ\text{C}$	Reference to 25°C , $\text{ID} = 1.0\text{mA}$
$R_{\text{DS}(\text{on})}$	Static Drain-to-Source On-State Resistance	—	—	0.0145	Ω	$\text{V}_{\text{GS}} = 12\text{V}, \text{ID} = 45\text{A}$ ④
$\text{V}_{\text{GS}(\text{th})}$	Gate Threshold Voltage	2.5	—	4.5	V	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}, \text{ID} = 1.0\text{mA}$
g_{fs}	Forward Transconductance	36	—	—	S (Ω)	$\text{V}_{\text{DS}} = 15\text{V}, \text{IDS} = 45\text{A}$ ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	$\text{V}_{\text{DS}} = 104\text{V}, \text{V}_{\text{GS}} = 0\text{V}$
		—	—	25		$\text{V}_{\text{DS}} = 104\text{V}, \text{V}_{\text{GS}} = 0\text{V}, \text{T}_j = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	$\text{V}_{\text{GS}} = 20\text{V}$
I_{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		$\text{V}_{\text{GS}} = -20\text{V}$
Q_g	Total Gate Charge	—	—	160	nC	$\text{V}_{\text{GS}} = 12\text{V}, \text{ID} = 45\text{A}$
Q_{gs}	Gate-to-Source Charge	—	—	55		$\text{V}_{\text{DS}} = 65\text{V}$
Q_{gd}	Gate-to-Drain ('Miller') Charge	—	—	75		
$t_{\text{d}(\text{on})}$	Turn-On Delay Time	—	—	35	ns	$\text{V}_{\text{DD}} = 65\text{V}, \text{ID} = 45\text{A}$ $\text{V}_{\text{GS}} = 12\text{V}, \text{R}_G = 2.35\Omega$
t_r	Rise Time	—	—	125		
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time	—	—	80		
t_f	Fall Time	—	—	50		
$L_S + L_D$	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm /0.25in. from package) to Source lead (6mm /0.25in from package) with Source wires internally bonded from Source Pin to Drain Pad
C_{iss}	Input Capacitance	—	5510	—	pF	$\text{V}_{\text{GS}} = 0\text{V}, \text{V}_{\text{DS}} = 25\text{V}$ $f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	1490	—		
C_{rss}	Reverse Transfer Capacitance	—	77	—		
R_g	Internal Gate Resistance	—	1.8	—	Ω	$f = 1.0\text{MHz}$, open drain

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	45*	A	
I_{SM}	Pulse Source Current (Body Diode) ①	—	—	180		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$\text{T}_j = 25^\circ\text{C}, I_S = 45\text{A}, \text{V}_{\text{GS}} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	—	300	ns	$\text{T}_j = 25^\circ\text{C}, I_F = 45\text{A}, dI/dt \leq 100\text{A}/\mu\text{s}$
Q_{RR}	Reverse Recovery Charge	—	—	3.1	μC	$\text{V}_{\text{DD}} \leq 25\text{V}$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

* Current is limited by package

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R_{thJC}	Junction-to-Case	—	—	0.60	$^\circ\text{C/W}$	Typical socket mount
R_{thCS}	Case-to-Sink	—	0.21	—		
R_{thJA}	Junction-to-Ambient	—	—	48		

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

Radiation Characteristics

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International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ $T_j = 25^\circ\text{C}$, Post Total Dose Irradiation ^{⑤⑥}

	Parameter	100K Rads (Si)		Units	Test Conditions ^⑧
		Min	Max		
BV_{DSS}	Drain-to-Source Breakdown Voltage	130	—	V	$\text{V}_{\text{GS}} = 0\text{V}, \text{I}_D = 1.0\text{mA}$
$\text{V}_{\text{GS}(\text{th})}$	Gate Threshold Voltage	2.0	4.5		$\text{V}_{\text{GS}} = \text{V}_{\text{DS}}, \text{I}_D = 1.0\text{mA}$
I_{GSS}	Gate-to-Source Leakage Forward	—	100	nA	$\text{V}_{\text{GS}} = 20\text{V}$
I_{GSS}	Gate-to-Source Leakage Reverse	—	-100		$\text{V}_{\text{GS}} = -20\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current	—	10	μA	$\text{V}_{\text{DS}}=104\text{V}, \text{V}_{\text{GS}}=0\text{V}$
$\text{R}_{\text{DS}(\text{on})}$	Static Drain-to-Source ^④ On-State Resistance (TO-3)	—	0.0140	Ω	$\text{V}_{\text{GS}} = 12\text{V}, \text{I}_D = 45\text{A}$
$\text{R}_{\text{DS}(\text{on})}$	Static Drain-to-Source On-state ^④ Resistance (Low-Ohmic TO-254)	—	0.0145	Ω	$\text{V}_{\text{GS}} = 12\text{V}, \text{I}_D = 45\text{A}$
V_{SD}	Diode Forward Voltage ^④	—	1.2	V	$\text{V}_{\text{GS}} = 0\text{V}, \text{I}_D = 45\text{A}$

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET MeV/(mg/cm ²)	Energy (MeV)	Range (μm)	V_{DS} (V)				
				@ $\text{V}_{\text{GS}}=0\text{V}$	@ $\text{V}_{\text{GS}}=-5\text{V}$	@ $\text{V}_{\text{GS}}=-10\text{V}$	@ $\text{V}_{\text{GS}}=-15\text{V}$	@ $\text{V}_{\text{GS}}=-20\text{V}$
Br	36.7	309	39.5	130	130	130	130	130
I	59.8	341	32.5	130	130	130	100	50
Au	82.3	350	28.4	130	120	30	—	—

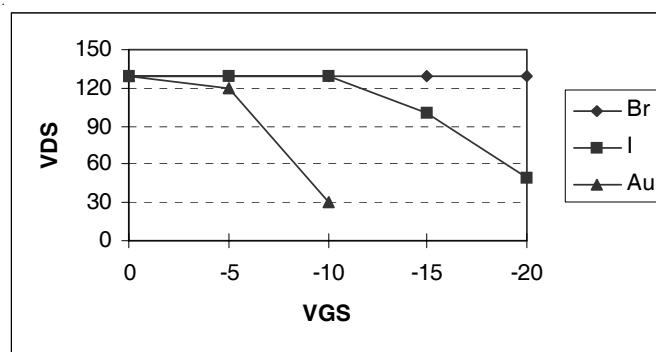


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

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Pre-Irradiation

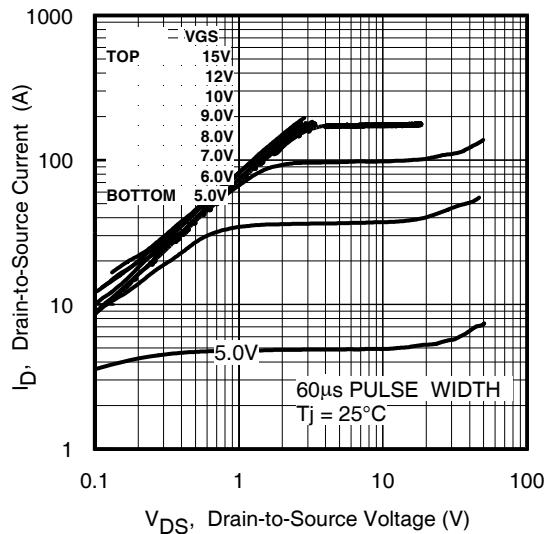


Fig 1. Typical Output Characteristics

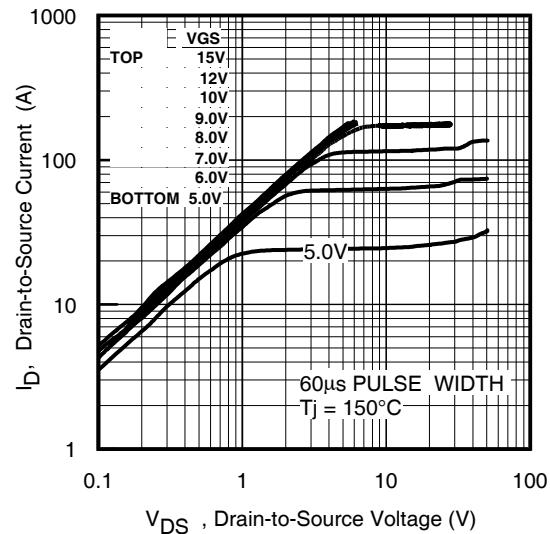


Fig 2. Typical Output Characteristics

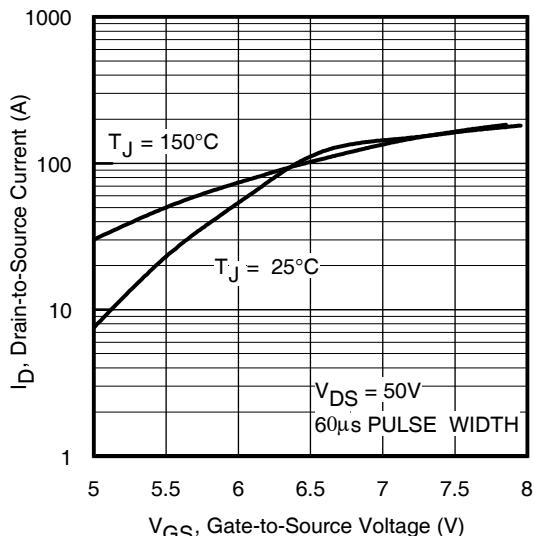


Fig 3. Typical Transfer Characteristics

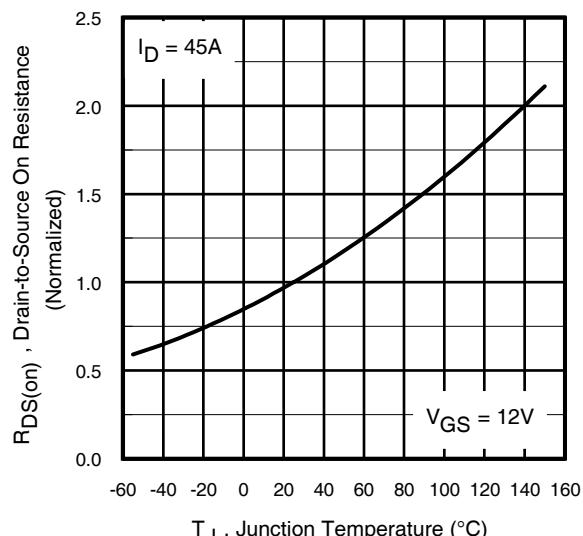


Fig 4. Normalized On-Resistance Vs. Temperature

Pre-Irradiation

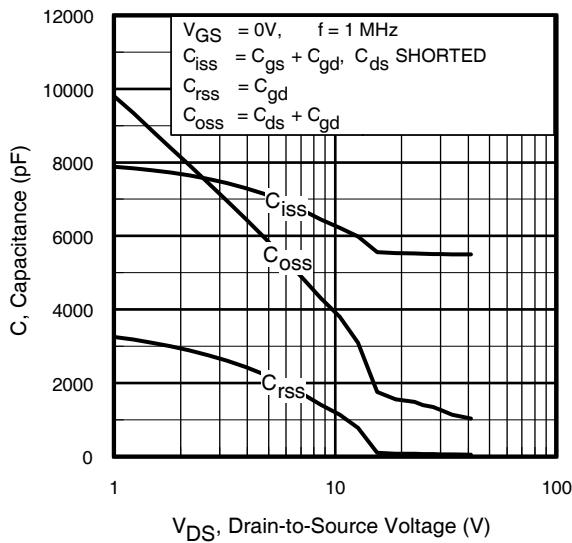


Fig 5. Typical Capacitance Vs.
Drain-to-Source Voltage

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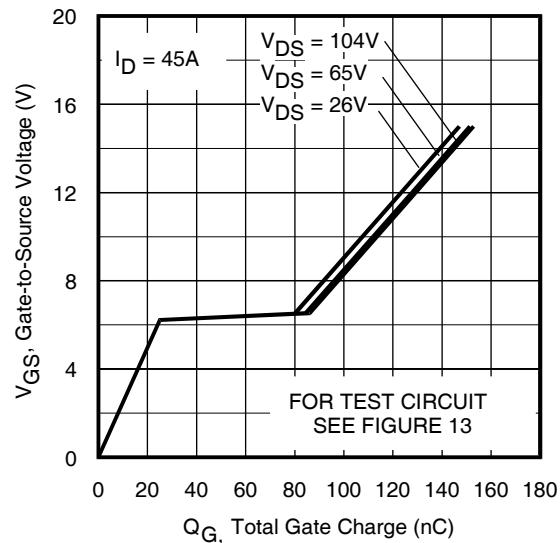


Fig 6. Typical Gate Charge Vs.
Gate-to-Source Voltage

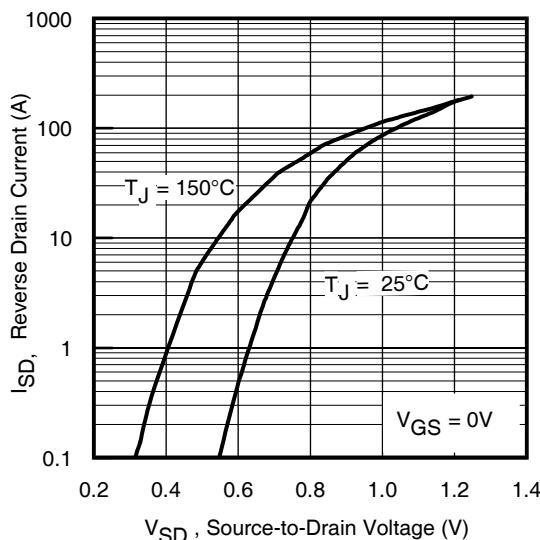


Fig 7. Typical Source-Drain Diode
Forward Voltage

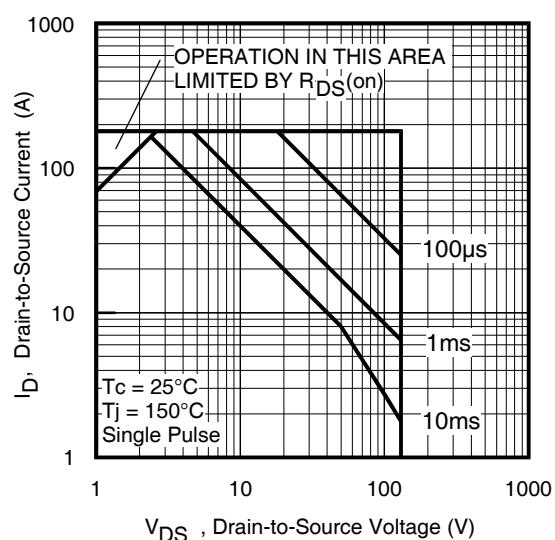


Fig 8. Maximum Safe Operating Area

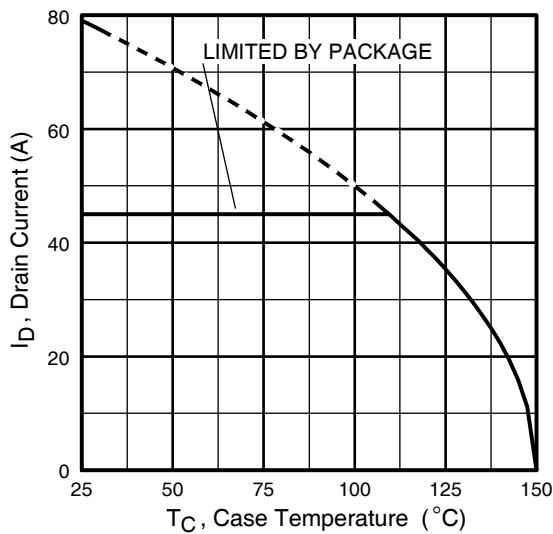


Fig 9. Maximum Drain Current Vs.
Case Temperature

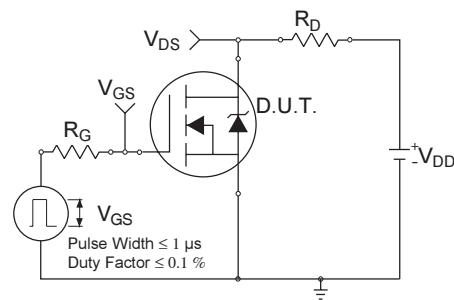


Fig 10a. Switching Time Test Circuit

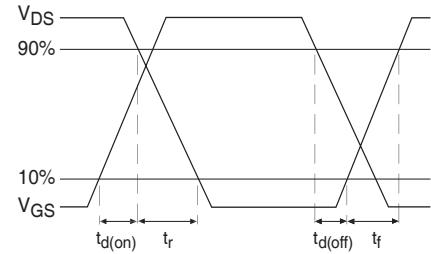


Fig 10b. Switching Time Waveforms

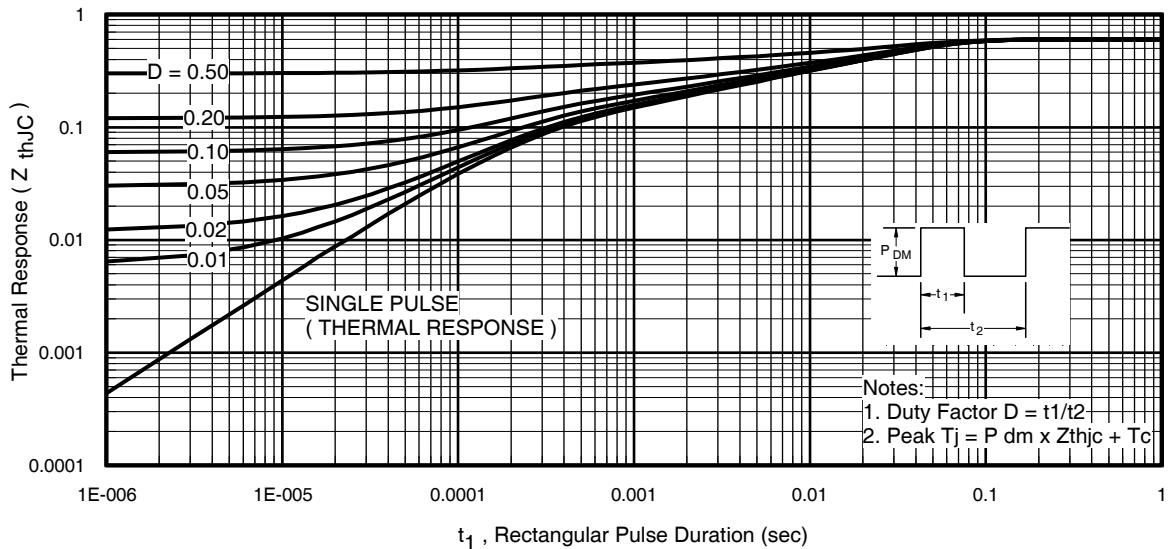


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Pre-Irradiation

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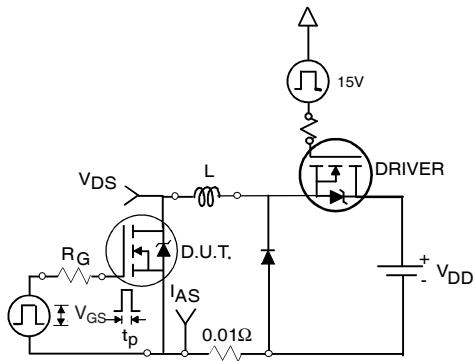


Fig 12a. Unclamped Inductive Test Circuit

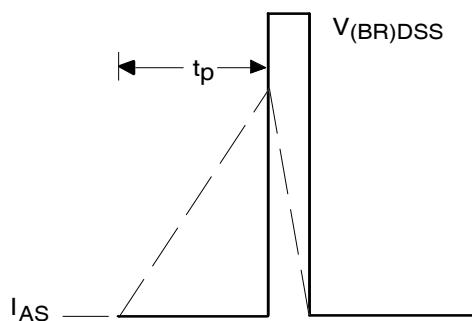


Fig 12b. Unclamped Inductive Waveforms

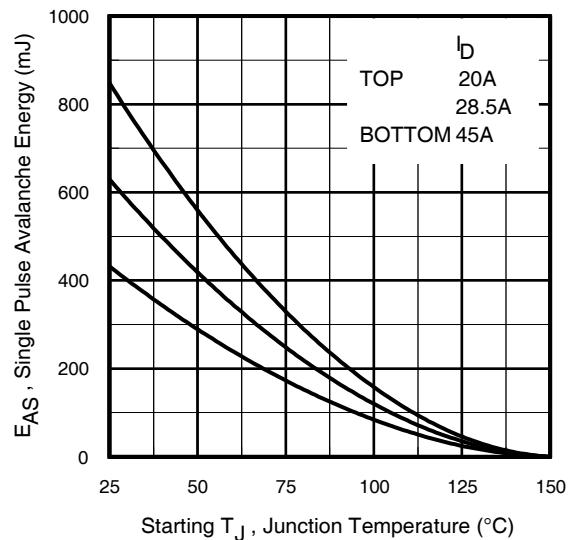


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

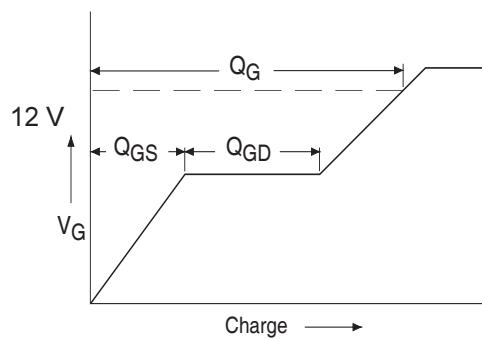


Fig 13a. Basic Gate Charge Waveform

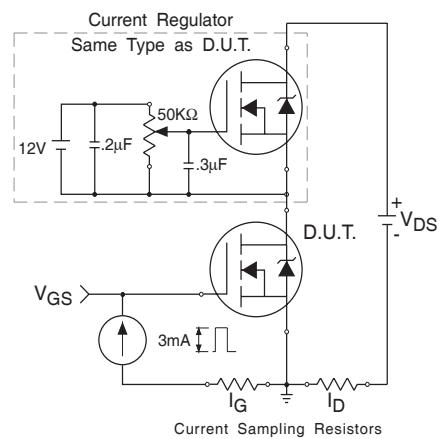


Fig 13b. Gate Charge Test Circuit

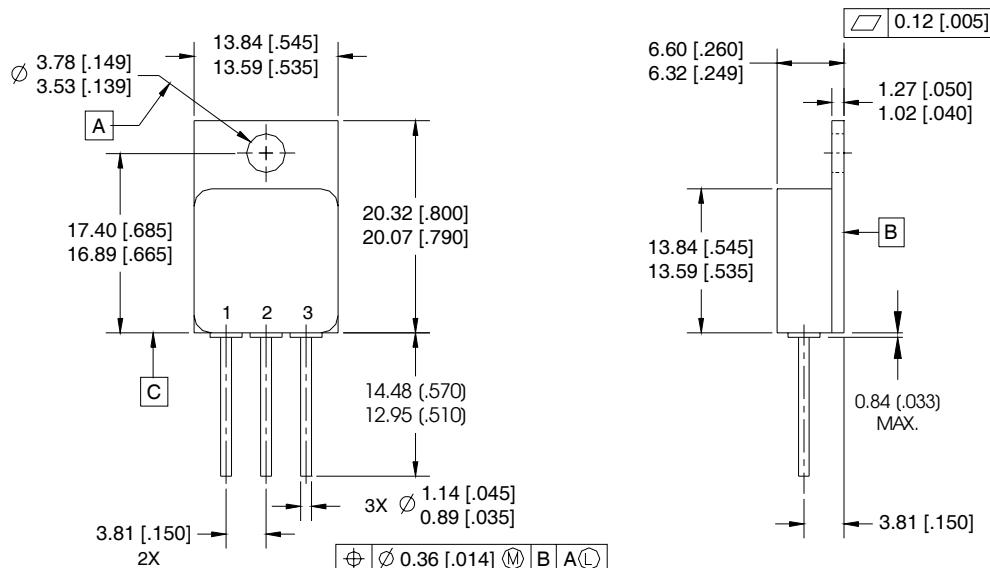
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Pre-Irradiation

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 50V$, starting $T_J = 25^\circ C$, $L = 0.43mH$
Peak $I_L = 45A$, $V_{GS} = 12V$
- ③ $ISD \leq 45A$, $dI/dt \leq 749A/\mu s$,
 $V_{DD} \leq 130V$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.**
104 volt V_{DS} applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — Low-Ohmic TO-254AA



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. CONTROLLING DIMENSION: INCH.
4. CONFORMS TO JEDEC OUTLINE TO-254AA.

PIN ASSIGNMENTS

- 1 = DRAIN
2 = SOURCE
3 = GATE

CAUTION

BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

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